

ABSTRACT OF THE DISCLOSURE

A semiconductor integrated circuit device includes
a semiconductor region of a first conductivity type.
A first insulated-gate field effect transistor having
5 a source/drain region of a second conductivity type
connected to an output terminal is formed on the
semiconductor region. Further, a semiconductor region
of a second conductivity type connected to the gate of
the transistor is formed adjacent to the source/drain
10 region of the transistor on the semiconductor region.